

General Description

The HSBA0139 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

The HSBA0139 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

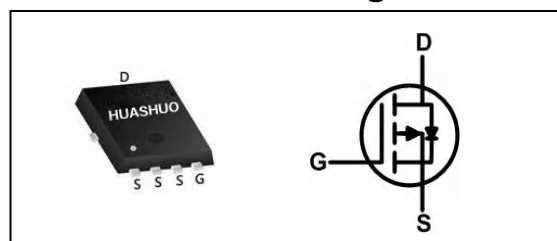
Features

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench Technology

Product Summary

V_{DS}	-100	V
$R_{DS(ON),typ}$	35	m Ω
I_D	-30	A

PRPAK5*6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-30	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-19	A
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-8	A
$I_D@T_A=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-6.5	A
I_{DM}	Pulsed Drain Current ²	-45	A
EAS	Single Pulse Avalanche Energy ³	345	mJ
I_{AS}	Avalanche Current	-28	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	83	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.22	$^{\circ}C/W$

P-Ch 100V Fast Switching MOSFETs
Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-10A$	---	35	42	$m\Omega$
		$V_{GS}=-4.5V, I_D=-8A$	---	40	50	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.8	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-100V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-50	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-10V, I_D=-10A$	---	32	---	S
Q_g	Total Gate Charge	$V_{DS}=-80V, V_{GS}=-10V, I_D=-14A$	---	92	---	nC
Q_{gs}	Gate-Source Charge		---	17.5	---	
Q_{gd}	Gate-Drain Charge		---	14	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-50V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-14A$	---	20.5	---	ns
T_r	Rise Time		---	32.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	123	---	
T_f	Fall Time		---	63.7	---	
C_{iss}	Input Capacitance	$V_{DS}=-25V, V_{GS}=0V, f=1\text{MHz}$	---	6516	---	pF
C_{oss}	Output Capacitance		---	223	---	
C_{rss}	Reverse Transfer Capacitance		---	125	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-30	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-14A, di/dt=-100A/\mu s, T_J=25^\circ\text{C}$	---	31.2	---	nS
Q_{rr}	Reverse Recovery Charge		---	31.97	---	nC

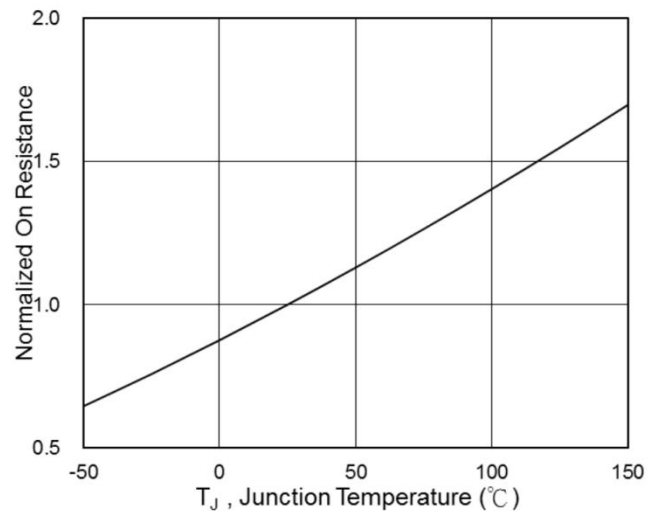
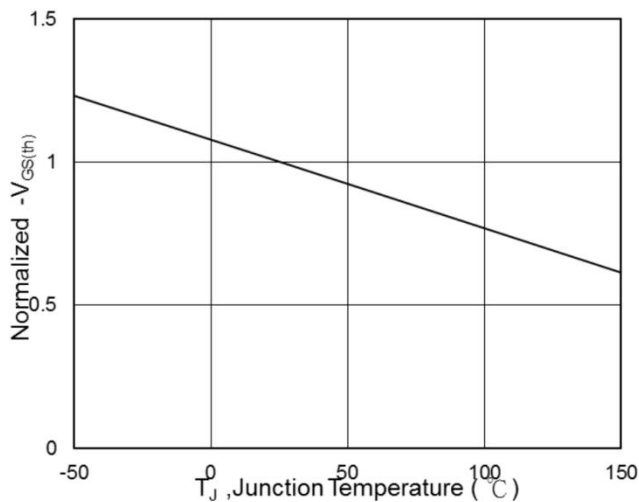
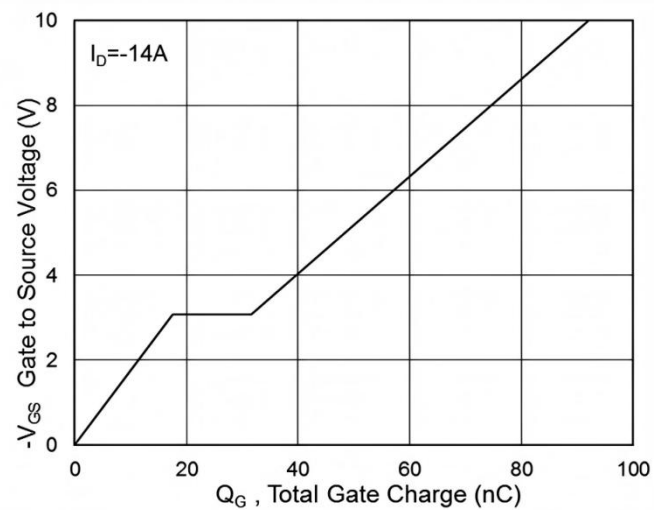
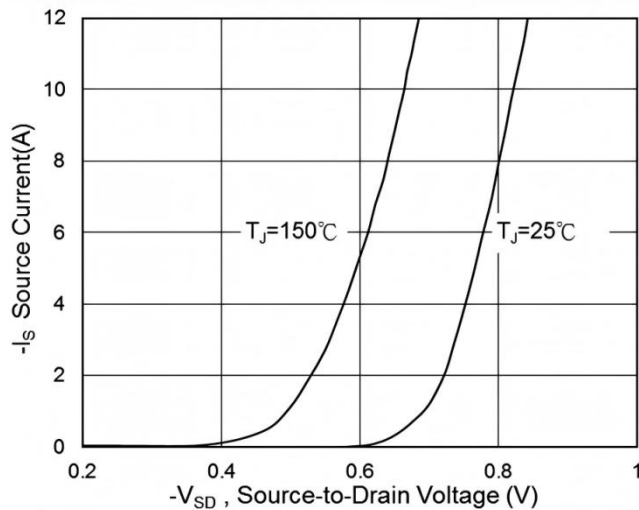
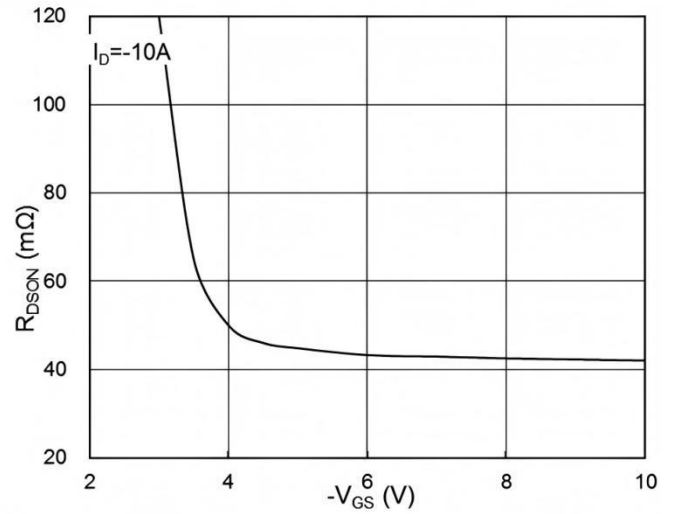
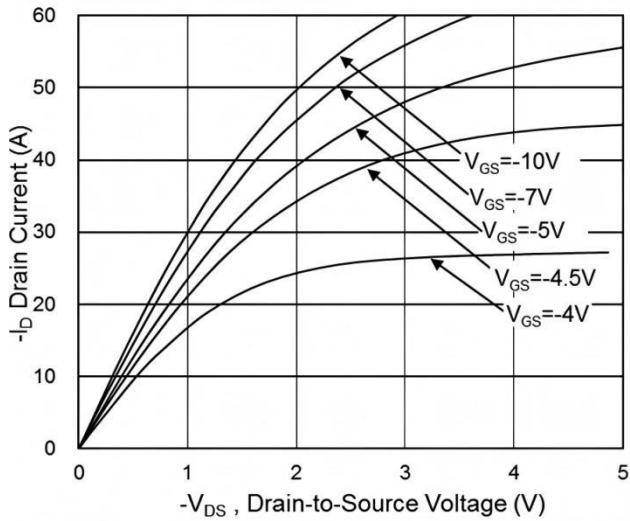
Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.88mH, I_{AS}=-28A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



P-Ch 100V Fast Switching MOSFETs

Typical Characteristics





P-Ch 100V Fast Switching MOSFETs

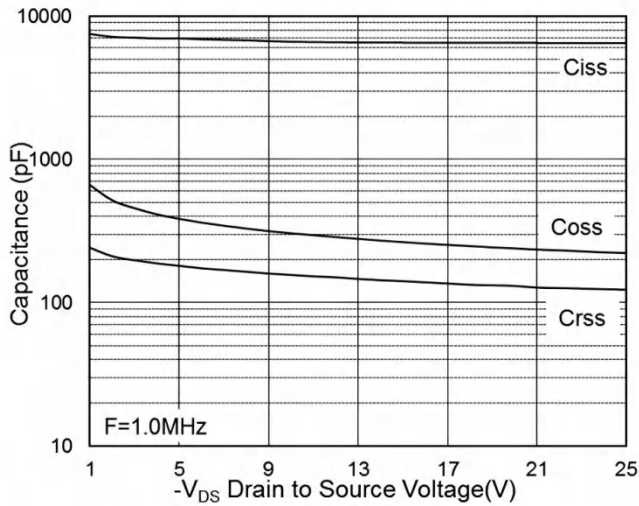


Fig.7 Capacitance

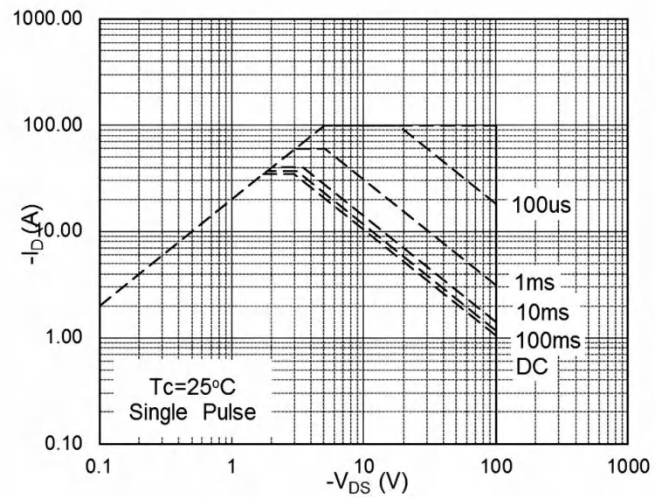


Fig.8 Safe Operating Area

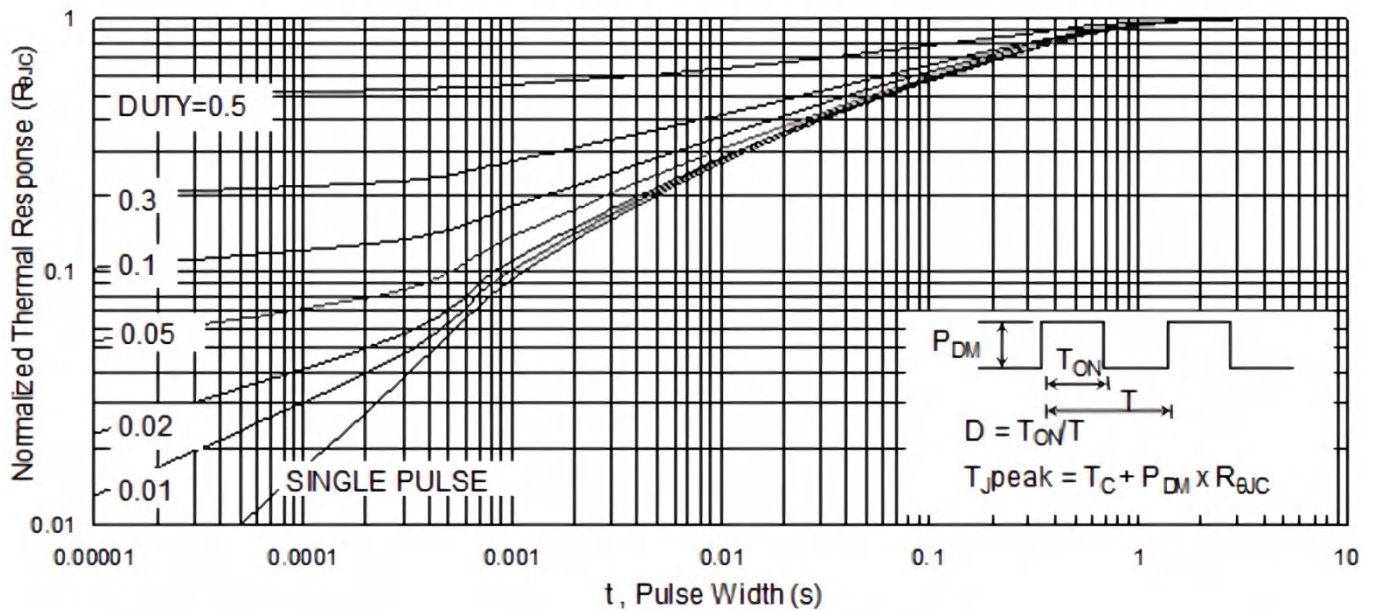


Fig.9 Normalized Maximum Transient Thermal Impedance

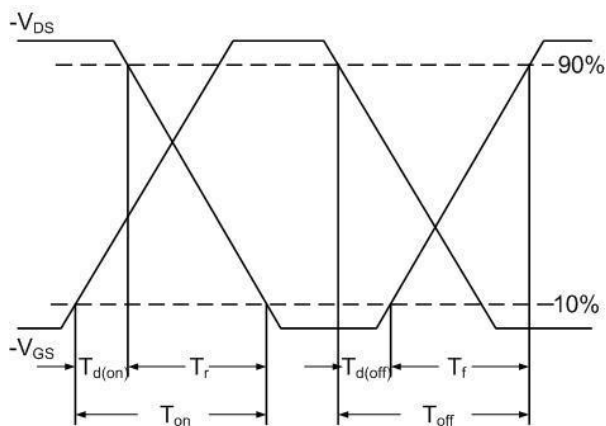


Fig.10 Switching Time Waveform

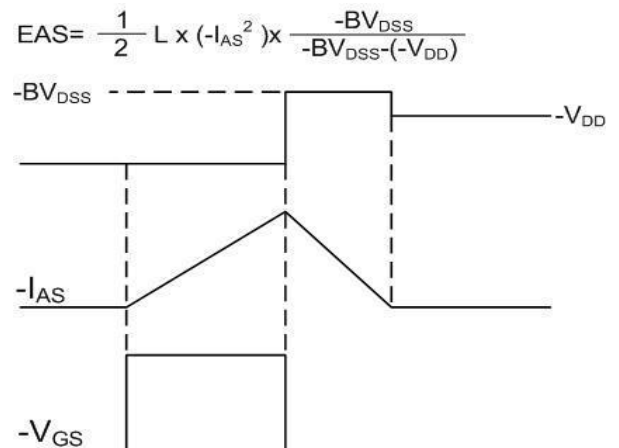
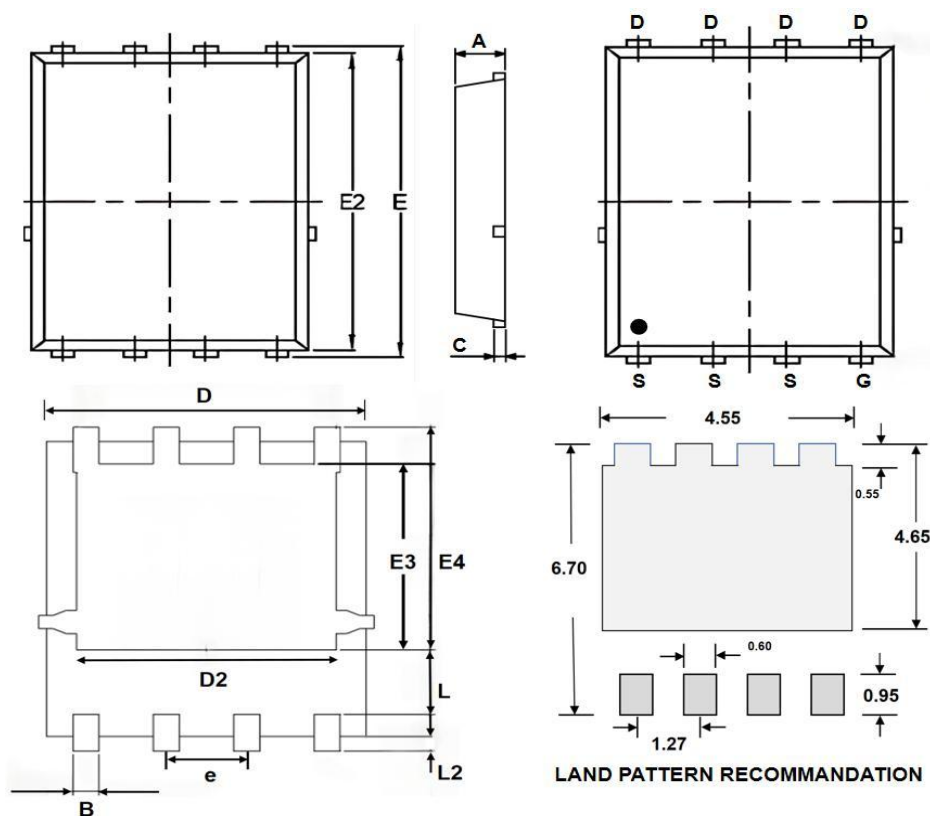


Fig.11 Unclamped Inductive Waveform

Ordering Information

Part Number	Package code	Packaging
HSBA0139	PRPAK5*6	3000/Tape&Reel

PRPAK5*6 Package Outline



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
B	0.25	--	0.51	0.012	--	0.020
C	0.15	--	0.35	0.006	--	0.014
D	4.80	--	5.45	0.189	--	0.209
D2	3.61	--	4.35	0.142	--	0.171
E	5.90	--	6.35	0.232	--	0.250
E2	5.42	--	6.06	0.213	--	0.232
E3	3.23	--	3.90	0.127	--	0.154
E4	3.69	--	4.55	0.145	--	0.179
L	0.61	--	1.80	0.024	--	0.071
L2	0.05	--	0.36	0.002	--	0.014
e	--	1.27	--	--	0.050	--

HSBA0139 Marking:

